





EH25 00 ET T TS -23.690M

Series —
RoHS Compliant (Pb-free) 5.0V 4 Pad 5mm x 7mm
Ceramic SMD HCMOS/TTL High Frequency Oscillator

Frequency Tolerance/Stability — ±100ppm Maximum

Operating Temperature Range – -40°C to +85°C Nominal Frequency 23.690MHz

└ Pin 1 Connection Tri-State (High Impedance)

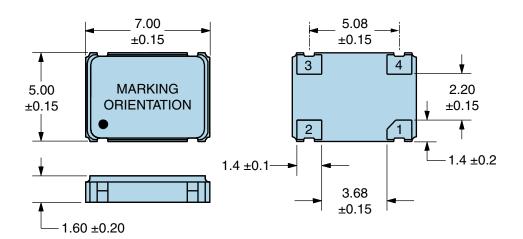
- Duty Cycle 50 ±5(%)

Operat Shock, ging at 25°C ±5ppm -40°C to perating Temperature Range 5.0Vdc put Current 50mA to put Current 50mA to put Voltage Logic High (Voh) 2.4Vdc put Voltage Logic Low (Vol) 0.4Vdc put Voltage Logic Low (Vol) 5ee/Fall Time 6nSec with High Cuty Cycle 50 ±5(to put Shock, and put Shock,	pm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the ting Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, and Vibration) Nyear Maximum to +85°C c ±10% Maximum (No Load) c Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)
Operat Shock, ging at 25°C ±5ppm -40°C to perating Temperature Range 5.0Vdc put Current 50mA lutput Voltage Logic High (Voh) 2.4Vdc put Current 0.4Vdc put Current 0.4Vdc put Current 0.4Vdc put Voltage Logic Low (Vol) 0.4Vdc put Voltage Logic Logi	ting Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, and Vibration) n/year Maximum to +85°C c ±10% Maximum (No Load)
2.40°C to	to +85°C c ±10% Maximum (No Load)
10 10 10 10 10 10 10 10	C ±10% Maximum (No Load)
put Current 50mA utput Voltage Logic High (Voh) 2.4Vdc utput Voltage Logic Low (Vol) 0.4Vdc se/Fall Time 6nSec with H0 uty Cycle 50 ±5(* pad Drive Capability 10TTL	Maximum (No Load)
utput Voltage Logic High (Voh) 2.4Vdc 0.4Vdc 0.4Vdc 6nSec with H0 uty Cycle 50 ±5(* ad Drive Capability 10TTL	
utput Voltage Logic Low (Vol) 0.4Vdc se/Fall Time 6nSec with H0 uty Cycle 50 ±5(* ad Drive Capability 10TTL	Minimum with TTL Load, Vdd-0.4Vdc Minimum, with HCMOS Load (IOH= -16mA)
se/Fall Time 6nSec with H0 uty Cycle 50 ±5(' add Drive Capability 10TTL	Will The Load, vad of the minimum with the Load (1811–1811)
with H0 saty Cycle 50 ±5(* pad Drive Capability 10TTL	c Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOH= +16mA)
pad Drive Capability 10TTL	Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform CMOS Load)
	%) (Measured at 50% of waveform with TTL Load or with HCMOS Load)
utput Logic Type CMOS	Load or 50pF HCMOS Load Maximum
n 1 Connection Tri-Sta	ite (High Impedance)
	dc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to output.
esolute Clock Jitter ±250ps	Sec Maximum, ±100pSec Typical
ne Sigma Clock Period Jitter ±50pS	ec Maximum, ±30pSec Typical
art Up Time 10mSe	ec Maximum
orage Temperature Range -55°C t	

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS		
ESD Susceptibility MIL-STD-883, Method 3015, Class 1, HBM: 1500V		
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Flammability	UL94-V0	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-883, Method 2002, Condition B	
Moisture Resistance	MIL-STD-883, Method 1004	
Moisture Sensitivity	J-STD-020, MSL 1	
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010, Condition B	
Vibration	MIL-STD-883, Method 2007, Condition A	



MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	23.690M
3	XXXXXX XXXXXX=Ecliptek Manufacturing Identifier

Suggested Solder Pad Layout

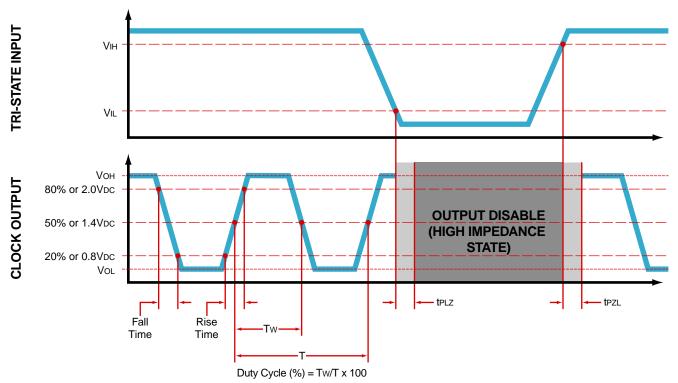
All Dimensions in Millimeters



All Tolerances are ±0.1



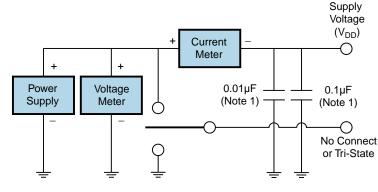
OUTPUT WAVEFORM & TIMING DIAGRAM

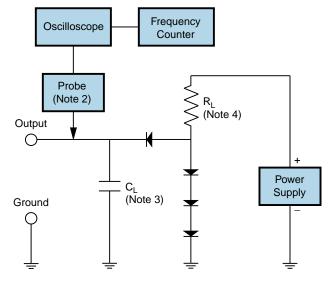


Test Circuit for TTL Output

Output Load Drive Capability	R _L Value (Ohms)	C _L Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability





Note 1: An external $0.1\mu F$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu F$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_{L} includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



Test Circuit for CMOS Output



Note 1: An external $0.1\mu\text{F}$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu\text{F}$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

<u> </u>	
T _s MAX to T _∟ (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _S MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
- Temperature Maximum (T _s MAX)	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (tp)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T _S MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
- Temperature Typical (T _S TYP)	150°C
- Temperature Maximum (T _s MAX)	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T _L to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)